

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Tetsushi TANIZAKI, et al.

Serial No.: 09/712,246

Filed: November 15, 2000

For: SEMICONDUCTOR MEMORY DEVICE WITH BUILT-IN SELF TEST CIRCUIT  
OPERATING AT HIGH RATE



Group Art Unit: 2818

Examiner:

PRELIMINARY AMENDMENT

Commissioner for Patents  
Washington, DC 20231

Sir:

Prior to examination of the above-referenced application, please amend the application as follows:

IN THE SPECIFICATION:

Page 23, line 6, change "Fig. 20" to --Fig. 21--;


line 9, change "Fig. 1" to --Fig. 2--.

REMARKS

Entry of this preliminary amendment is respectfully requested. An annex is attached herewith which includes a clean copy of the first paragraph as amended on page 23.

Respectfully submitted,

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